

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	30139	MOS and semiconductor and power and parallel	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2005/03/21 04:56
L2	2555	MOS and semiconductor same power same parallel	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2005/03/21 04:56
L3	685	MOS same semiconductor same power same parallel	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2005/03/21 05:14
L4	146	MOS same semiconductor same power same parallel and heat	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2005/03/21 05:31
L5	363	MOS with transistor and semiconductor same power same parallel and heat	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2005/03/21 05:32
L6	216	MOS with transistor same power and semiconductor same power same parallel and heat	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2005/03/21 05:32

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